

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
200V	0.5Ω@10V	5A

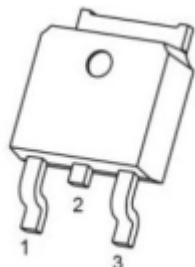
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Application

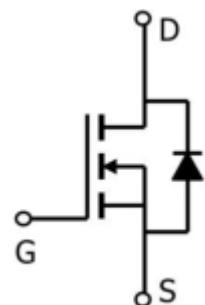
- DC-DC Converter
- Ideal for high-frequency switching and synchronous rectification

Package

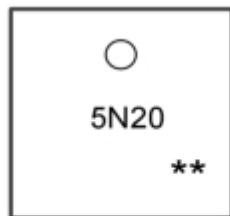


TO-252-2L(G:1 D:2 S:3)

Circuit diagram



Marking



5N20
** =Device Code
 =Week Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ¹ ($T_c = 25^\circ\text{C}$)	I_D	5	A
Pulsed Drain Current ²	I_{DM}	20	A
Single Pulse Avalanche Energy ³	E_{AS}	101	mJ
Total Power Dissipation($T_c = 25^\circ\text{C}$)	P_D	40	W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	3.12	$^\circ\text{C} / \text{W}$
Storage Temperature Range	T_{STG}	-55~ +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55~ +150	$^\circ\text{C}$



ZL MOSFET

ZL5N20

Electrical characteristics

(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	200			V
Bvdss Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250uA, Reference 25 °C		0.26		V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 200V, V _{GS} = 0V T _J = 25°C			1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V			±100	uA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
Static Drain-Source on-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 3A		0.5	0.6	Ω
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		255		pF
Output Capacitance	C _{oss}			52		
Reverse Transfer Capacitance	C _{rss}			8		
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 100V, V _{GS} = 10V, I _D = 4.8A		7		nC
Gate-Source Charge	Q _{gs}			2		
Gate-Drain Charge	Q _{gd}			3		
Turn-On Delay Time	T _{d(on)}	V _{DD} = 100V, V _{GS} = 10V, R _G = 10Ω, I _D = 4.8A		7		nS
Rise Time	T _r			13		
Turn-Off Delay Time	T _{d(off)}			27		
Fall Time	T _f			11		

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is ID=5A, L=10mH

Typical Characteristics

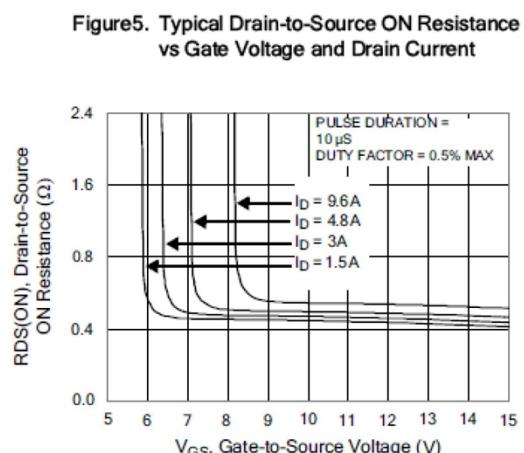
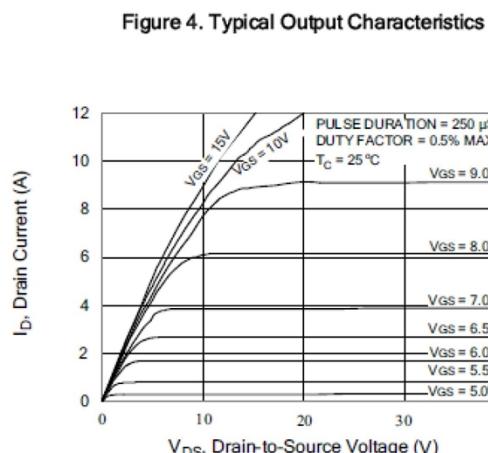
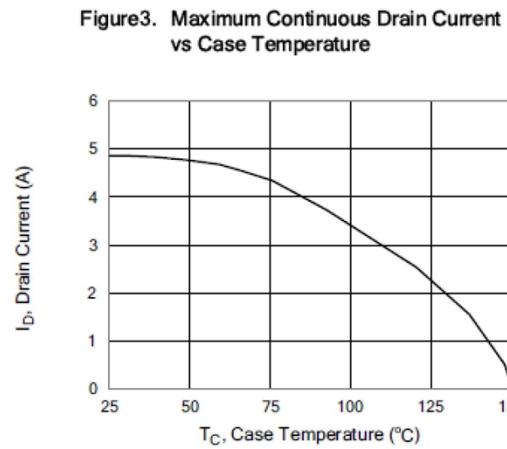
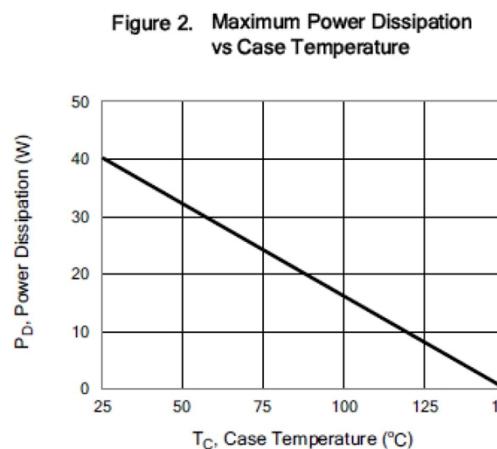
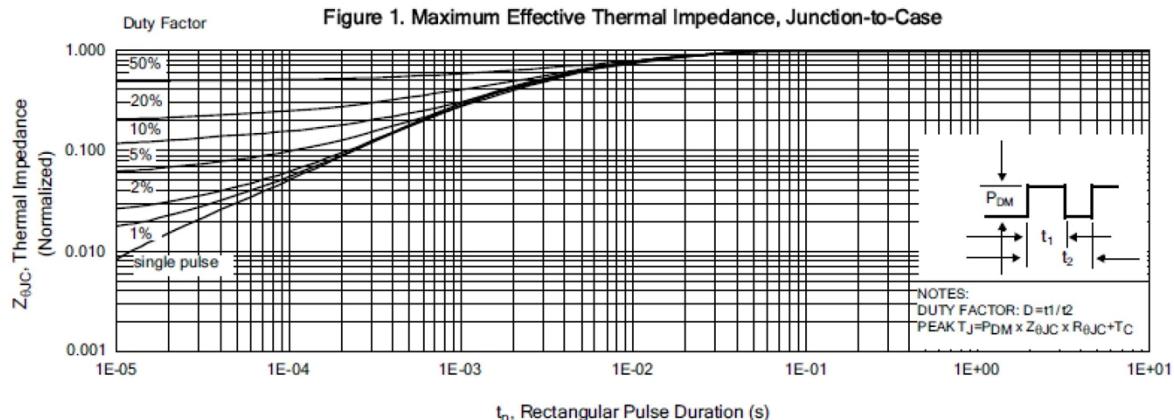


Figure 6. Maximum Peak Current Capability

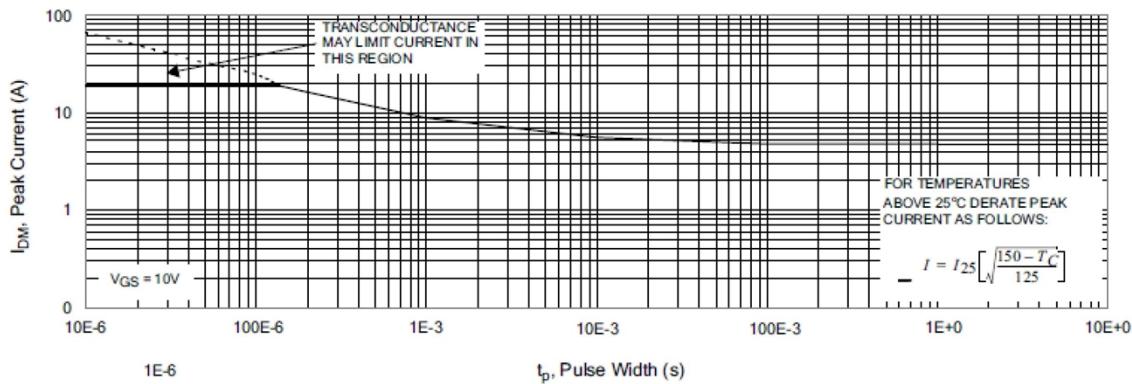


Figure 7. Typical Transfer Characteristics

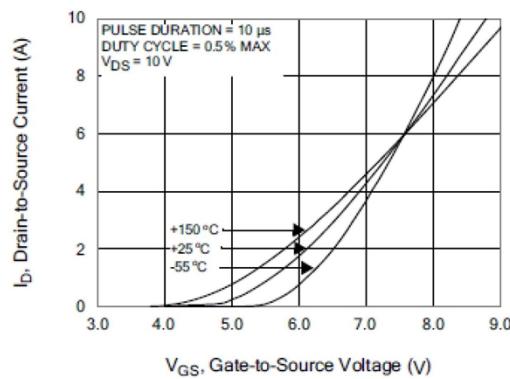


Figure 8. Unclamped Inductive Switching Capability

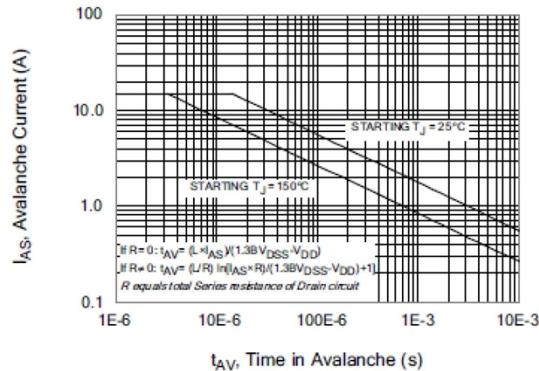


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

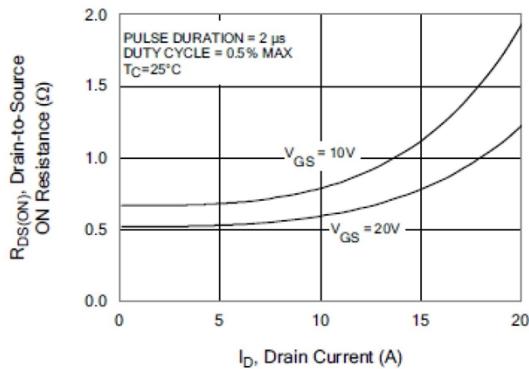


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

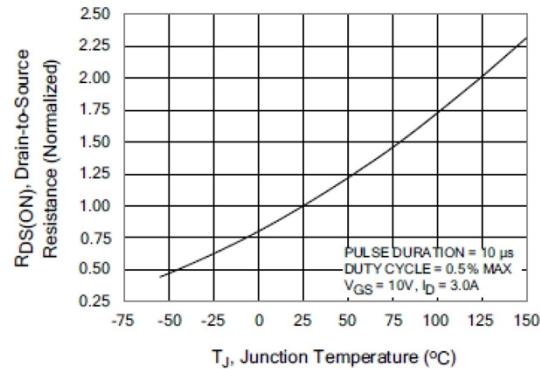


Figure 11. Typical Breakdown Voltage vs Junction Temperature

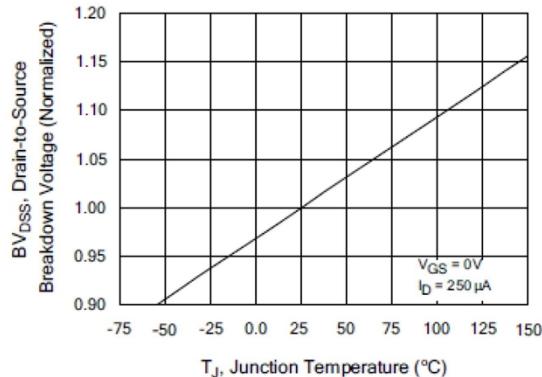


Figure 13. Maximum Forward Bias Safe Operating Area

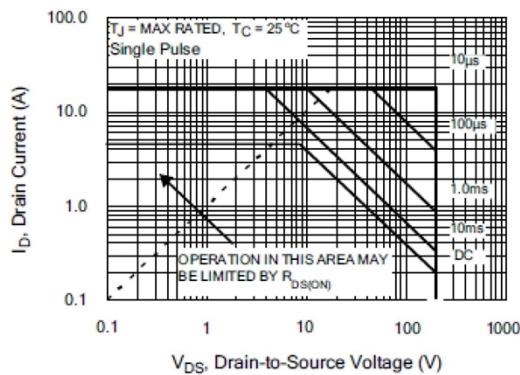


Figure 12. Typical Threshold Voltage vs Junction Temperature

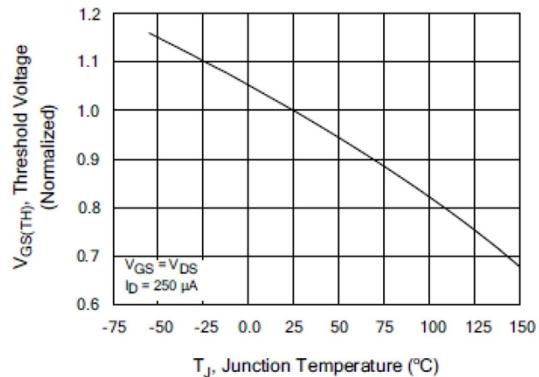


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

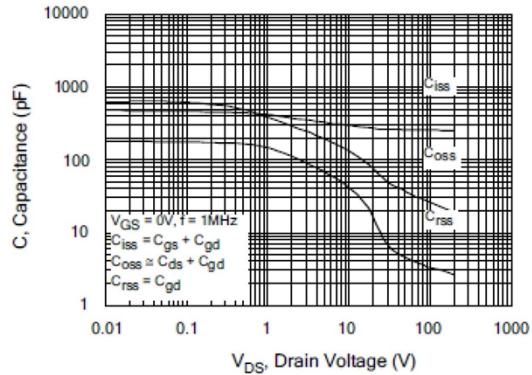


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

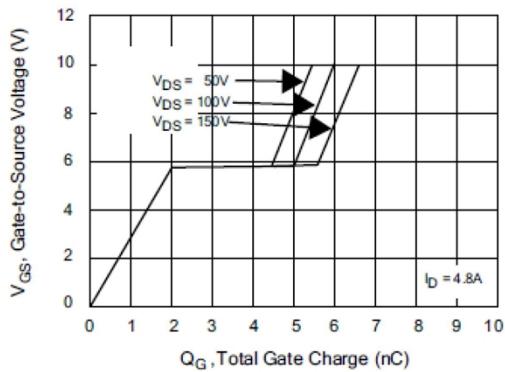
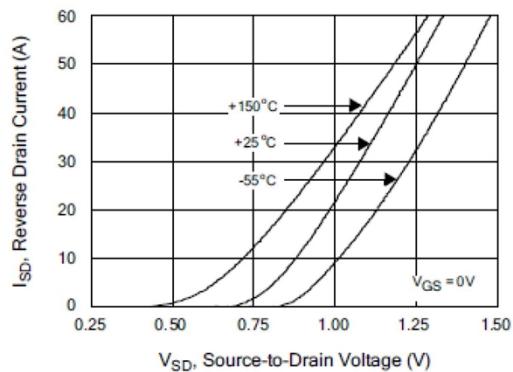
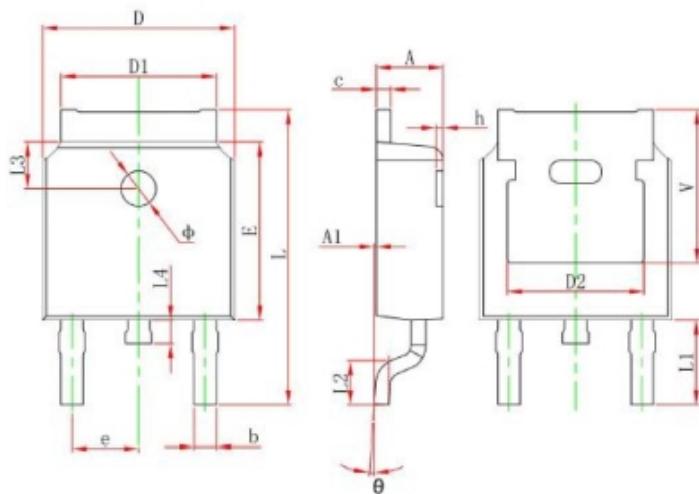


Figure 16. Typical Body Diode Transfer Characteristics



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	